

In the Claims:

1. (Currently amended) A radiation-emitting thin-film semiconductor component with a multilayer structure (12) based on GaN, which contains an active, radiation-generating layer (14) and has a first main area (16) and a second main area (18) - remote from the first main area - for coupling out the radiation generated in the active, radiation-generating layer,

wherein ~~characterized in that~~

the first main area (16) of the multilayer structure (12) is coupled to a reflective layer or interface, and the region (22) of the multilayer structure that adjoins the second main area (18) of the multilayer structure is patterned one- or two-dimensionally.

2. (Currently amended) The semiconductor component as claimed in claim 1,

wherein ~~characterized in that~~

the region (22) of the multilayer structure that adjoins the second main area (18) of the multilayer structure (12) has convex elevations (26).

3. (Currently amended) The semiconductor component as claimed in claim 2,

wherein ~~characterized in that~~

the elevations (26) have the form of truncated pyramids or truncated cones or a trapezoidal cross-sectional form.

4. (Currently amended) The semiconductor component as claimed in claim 2,
wherein ~~characterized in that~~
the elevations (26) have the form of cones or a triangular cross-sectional form.

5. (Currently amended) The semiconductor component as claimed in claim 2,
wherein ~~characterized in that~~
the elevations (26) have the form of sphere segments or a circle segment cross-sectional form.

6. (Currently amended) The semiconductor component as claimed in claim 2
~~one of claims 2 to 5,~~
wherein ~~characterized in that~~
the elevations (26) have an aperture angle (α) of between approximately 30° and approximately 70°.

7. (Currently amended) The semiconductor component as claimed in claim 6,
wherein ~~characterized in that~~
the elevations (26) have an aperture angle (α) of between approximately 40° and approximately 50°.

8. (Currently amended) The semiconductor component as claimed in claim 2
~~one of claims 2 to 7,~~

wherein ~~characterized in that~~

the height (h1) of the elevations (26) is at least as large as the height (h2) of a plane region (20) of the multilayer structure (12) between the active, radiation-generating layer (14) and the elevations.

9. (Currently amended) The semiconductor component as claimed in claim 8,

wherein ~~characterized in that~~

the height (h1) of the elevations (26) is approximately twice as large as the height (h2) of the plane region (20) of the multilayer structure between the active, radiation-generating layer and the elevations.

10. (Currently amended) The semiconductor component as claimed in claim 2
~~in one of claims 2 to 9,~~

wherein ~~characterized in that~~

a grid dimension (d) of the elevations (26) is at most approximately five times as large as the height (h1) of the elevations.

11. (Currently amended) The semiconductor component as claimed in claim 10,

wherein ~~characterized in that~~

the grid dimension (d) of the elevations is at most approximately three times as large as the height (h1) of the elevations.

12. (Currently amended) The semiconductor component as claimed in claim 1
~~one of claims 1 to 11,~~

wherein ~~characterized in that~~

the layer (28) or interface coupled to the first main area (16) of the multilayer structure (12) has a degree of reflection of at least 70%.

13. (Currently amended) The semiconductor component as claimed in claim 1
~~one of claims 1 to 11,~~

wherein ~~characterized in that~~

the layer (28) or interface coupled to the first main area (16) of the multilayer structure (12) has a degree of reflection of at least 85%.

14. (Currently amended) The semiconductor component as claimed claim 1 in
~~one of claims 1 to 13,~~

wherein ~~characterized in that~~

the multilayer structure (12) is applied by its first main area (16) directly or via a reflective layer (28) on a carrier substrate (30).

15. (Currently amended) The semiconductor component as claimed in claim 14,
wherein ~~characterized in that~~
the reflective layer or the carrier substrate also serves as a contact area of the semiconductor component.

16. (Currently amended) The semiconductor component as claimed ~~in one of~~
~~claims 1 to 15~~ claim 1,

wherein ~~characterized in that~~

a conductive, transparent layer is applied on the second main area (18) of the multilayer structure (12).

17. (Currently amended) The semiconductor component as claimed in claim 1
~~one of claims 1 to 16~~,

wherein ~~characterized in that~~

a transparent protective layer (32) is applied on the second main area (18) of the multilayer structure (12).

18. (Currently amended) A radiation-emitting thin-film semiconductor component with a multilayer structure (12) based on GaN, which contains an active, radiation-generating layer (14) and has a first main area (16) and a second main area (18) - remote from the first main area - for coupling out the radiation generated in the active, radiation-generating layer,

wherein ~~characterized in that~~

the first main area (16) of the multilayer structure (12) is coupled to a reflective layer (28) or interface, and a transparent layer (32) is provided between the first main area (16) of the multilayer structure and the reflective layer or interface, said transparent layer being patterned one- or two-dimensionally.

19. (Currently amended) The semiconductor component as claimed in claim 18,
wherein ~~characterized in that~~

the transparent layer (34) is conductive.

20. (Currently amended) The semiconductor component as claimed in claim 18
~~or 19,~~

wherein ~~characterized in that~~

the transparent layer (34) between the first main area (16) of the multilayer
structure (12) and the reflective layer (28) or interface has convex elevations (26').

21. (Currently amended) The semiconductor component as claimed in claim 20,
wherein ~~characterized in that~~

the elevations (26') have the form of truncated pyramids or truncated cones or a
trapezoidal cross-sectional form.

22. (Currently amended) The semiconductor component as claimed in claim 20
~~or 21,~~

wherein ~~characterized in that~~

the elevations (26') have an aperture angle (α) of between approximately 30° and
approximately 70°.

23. (Currently amended) The semiconductor component as claimed in claim 20 or 21,

wherein ~~characterized in that~~

the elevations (26') have an aperture angle (α) of between approximately 40° and approximately 50°.

24. (Currently amended) The semiconductor component as claimed in claim 20 ~~one of claims 20 to 23,~~

wherein ~~characterized in that~~

the height (h1) of the elevations (26') is at least as large as the height (h2) of a plane region (35) of the multilayer structure (12) between the active, radiation-generating layer (14) and the elevations.

25. (Currently amended) The semiconductor component as claimed in claim 24,

wherein ~~characterized in that~~

the height (h1) of the elevations (26') is approximately twice as large as the height (h2) of the plane region (35) of the multilayer structure between the active, radiation-generating layer and the elevations.

26. (Currently amended) The semiconductor component as claimed in claim 20
~~one of claims 20 to 25,~~

~~characterized in that~~

a grid dimension (d) of the elevations (26') is at most approximately five times as large as the height (h1) of the elevations.

27. (Currently amended) The semiconductor component as claimed in claim 26,

wherein ~~characterized in that~~

the grid dimension (d) of the elevations is at most approximately three times as large as the height (h1) of the elevations.

28. (Currently amended) The semiconductor component as claimed in ~~one of~~
~~claims 18 to 27~~ claim 18,

wherein ~~characterized in that~~

the layer or interface coupled to the first main area (16) of the multilayer structure (12) has a degree of reflection of at least 70%.

29. (Currently amended) The semiconductor component as claimed in claim 28,

wherein ~~characterized in that~~

the layer or interface coupled to the first main area (16) of the multilayer structure (12) has a degree of reflection of at least 85%.

30. (Currently amended) The semiconductor component as claimed in claim 18
~~one of claims 18 to 29,~~

wherein ~~characterized in that~~

the reflective layer (28) is applied on a carrier substrate (30) or the reflective interface is formed by a carrier substrate (30).

31. (Currently amended) The semiconductor component as claimed in claim 30,

wherein ~~characterized in that~~

the reflective layer or the carrier substrate also serves as a contact area of the semiconductor component.

32. (Currently amended) The semiconductor component as claimed in claim 18
~~one of claims 18 to 31,~~

wherein ~~characterized in that~~

a transparent protective layer is applied on the second main area (18) of the multilayer structure (12).